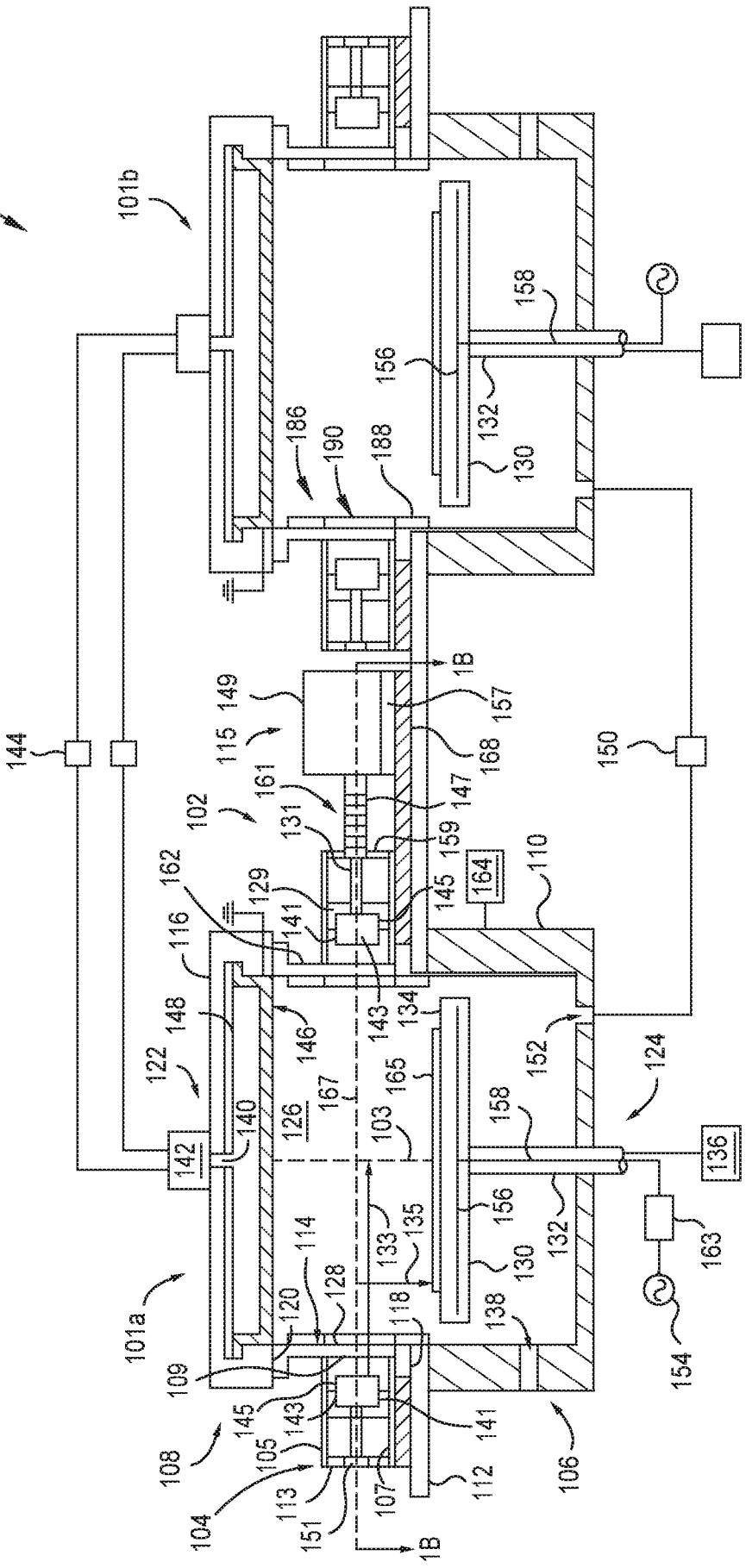
100
101b
101a
102
104
105
106
107
108
109
110
112
113
114
115
116
118
120
122
124
126
128
129
130
131
132
133
134
135
136
138
140
141
142
143
144
145
146
147
148
149
150
151
152
154
156
157
158
159
161
162
163
164
165
167
168
186
188
190
1B
1B

FIG. 1A

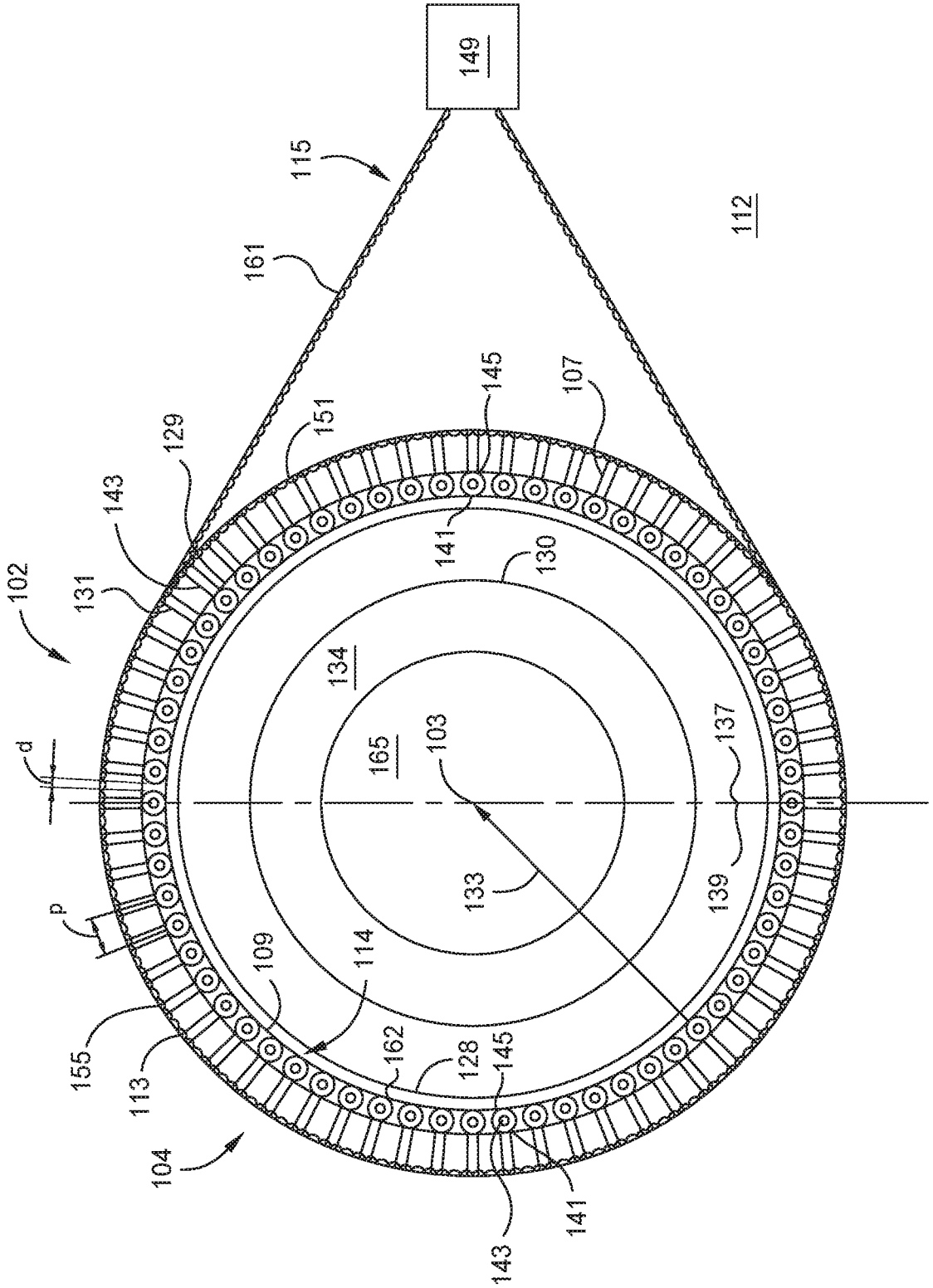
149
115
112
161
145
107
151
129
143
141
130
102
131
134
165
103
137
d
133
139
p
109
114
155
162
128
145
113
104
143
141

FIG. 1B

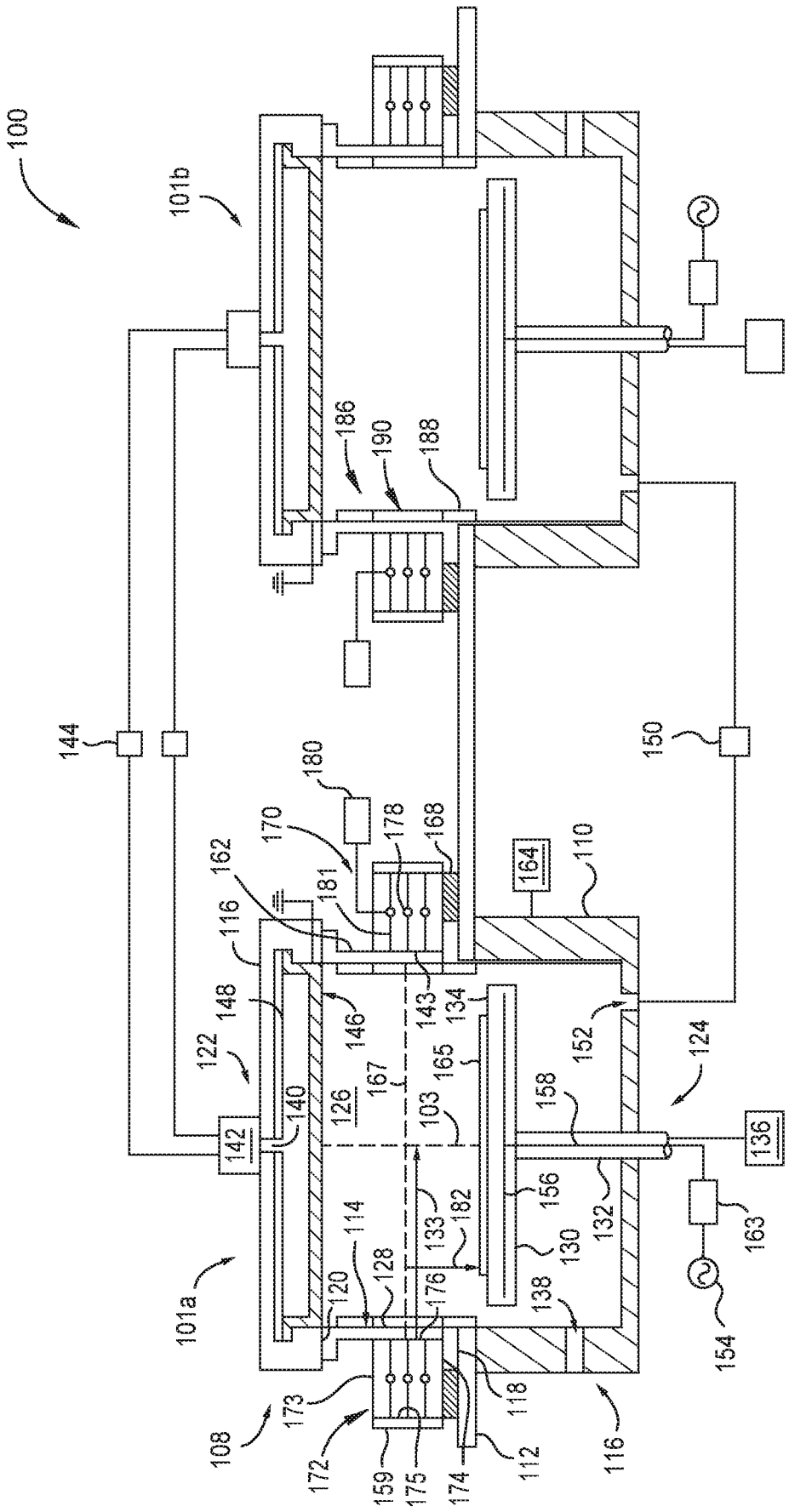
100
101b
186
190
188
144
150
180
170
178
168
162
181
164
110
116
148
146
143
134
152
122
165
124
167
126
158
140
103
142
136
156
132
133
182
163
114
130
101a
120
128
176
138
154
173
118
108
172
159
175
174
112
116

FIG. 1C

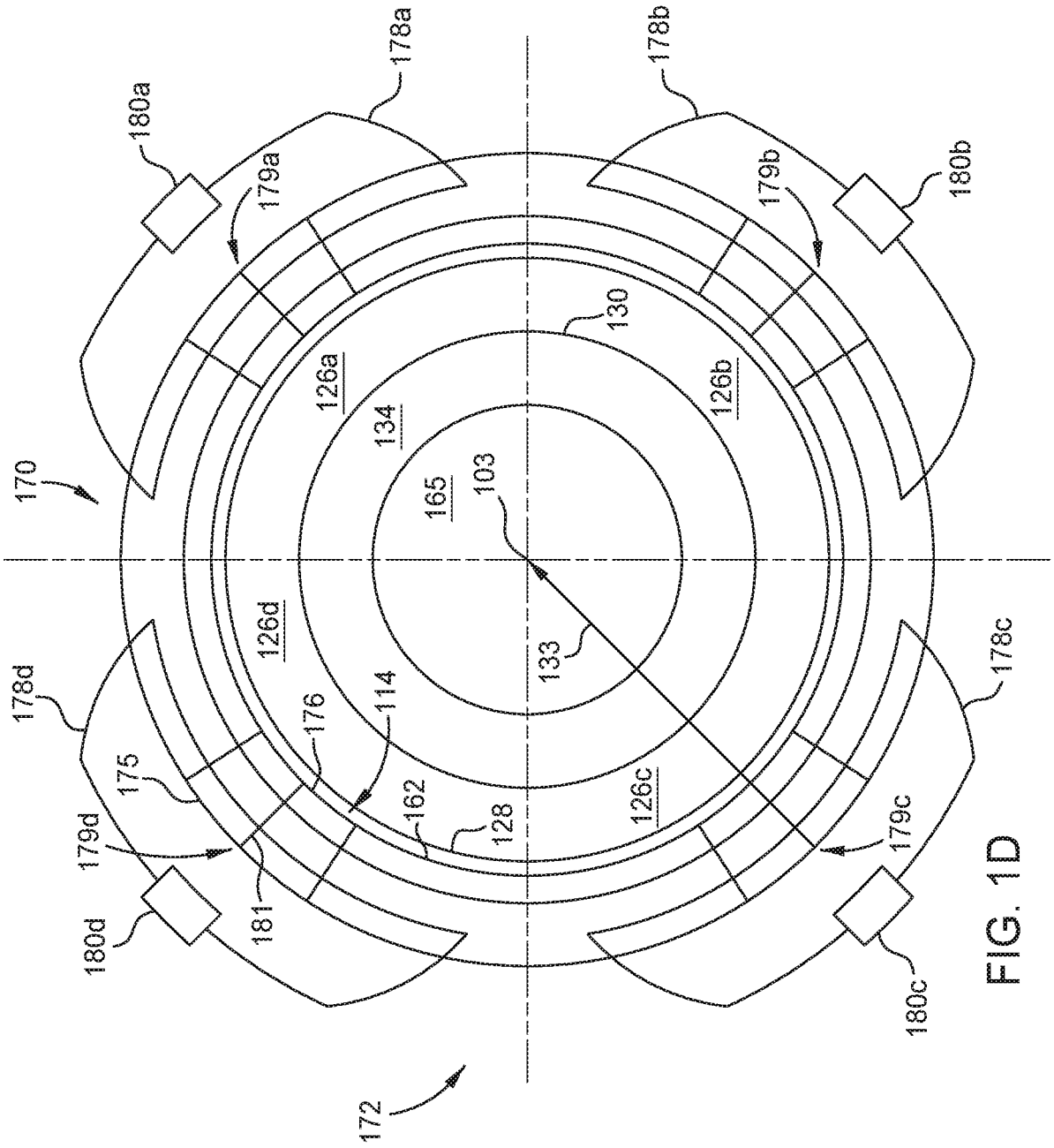
170
172
178a
178b
178c
178d
180a
180b
180c
180d
179a
179b
179c
179d
126a
126b
126c
126d
130
134
165
103
133
114
176
175
162
128
181

FIG. 1D

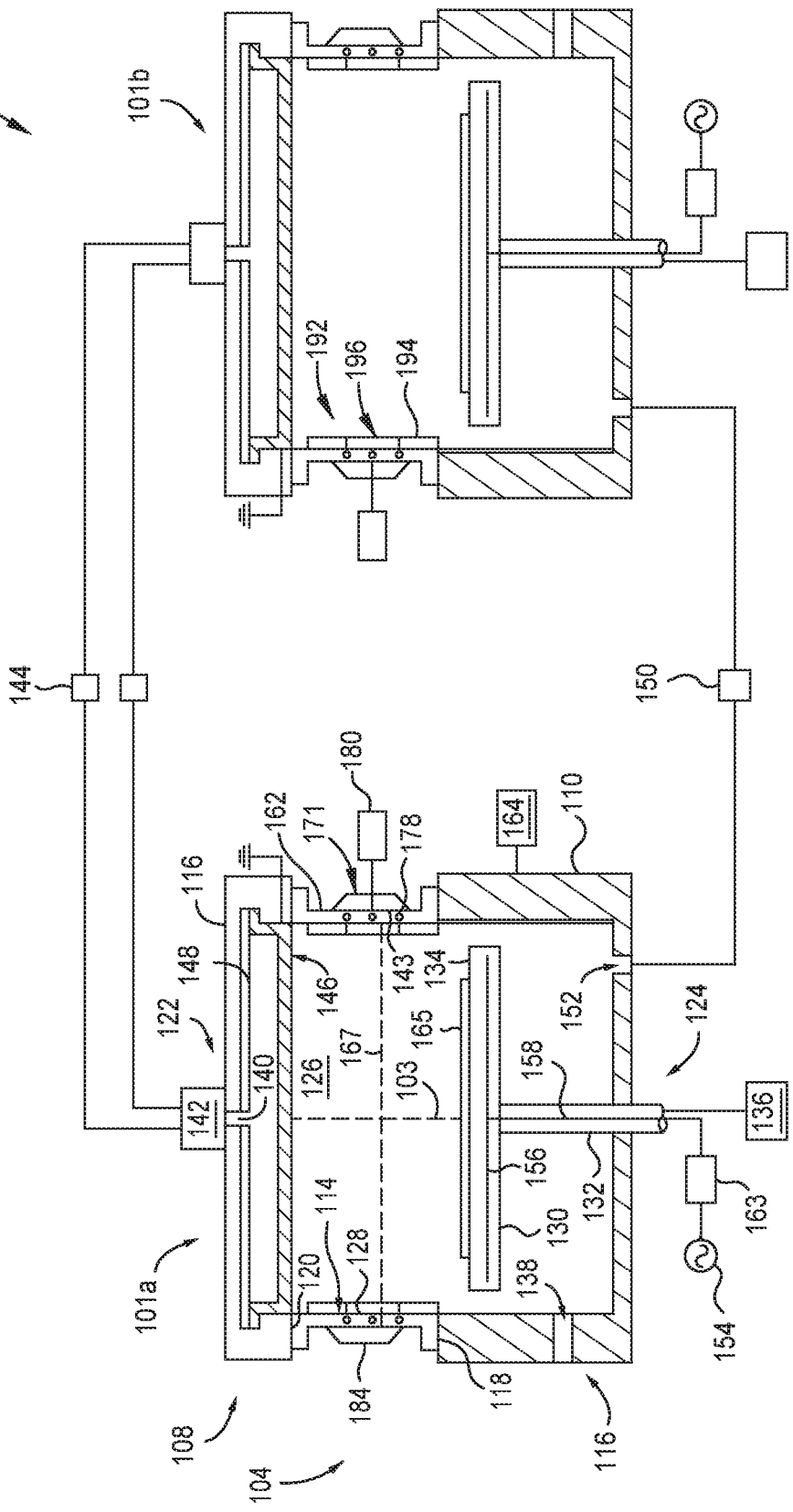
100
101b
192
196
194
144
150
180
162
171
178
164
110
116
148
146
143
134
122
152
124
165
167
126
140
103
158
142
136
156
132
163
114
130
101a
120
128
138
154
184
118
108
116
104

FIG. 1E

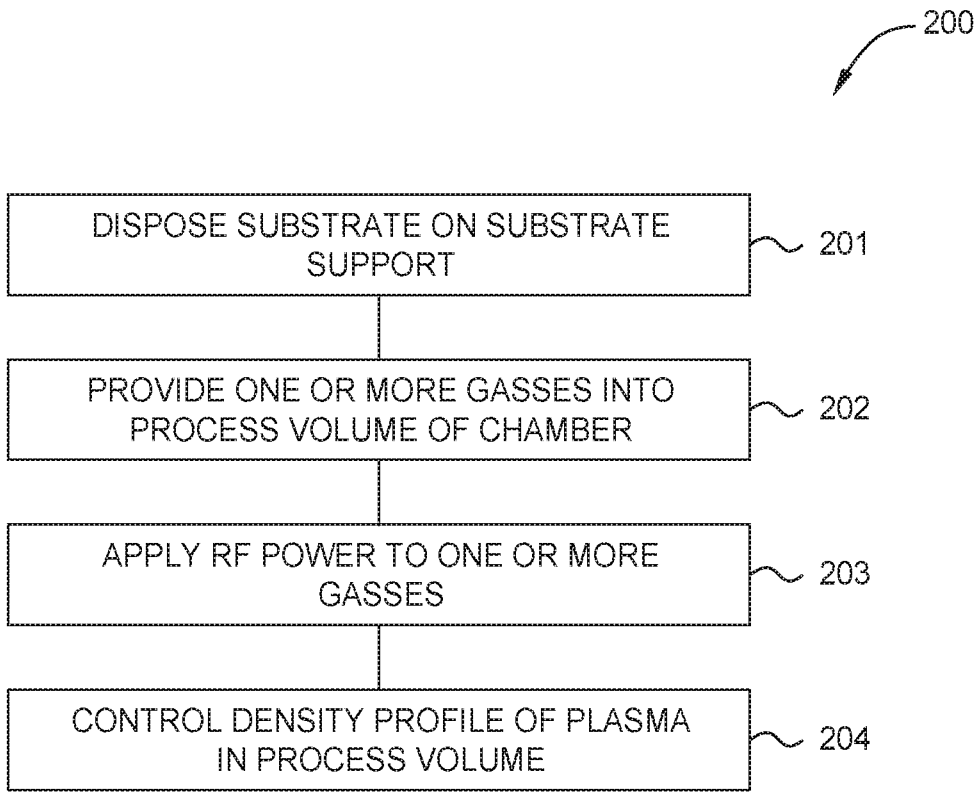
200
DISPOSE SUBSTRATE ON SUBSTRATE SUPPORT
201
PROVIDE ONE OR MORE GASSES INTO PROCESS VOLUME OF CHAMBER
202
APPLY RF POWER TO ONE OR MORE GASSES
203
CONTROL DENSITY PROFILE OF PLASMA IN PROCESS VOLUME
204

FIG. 2

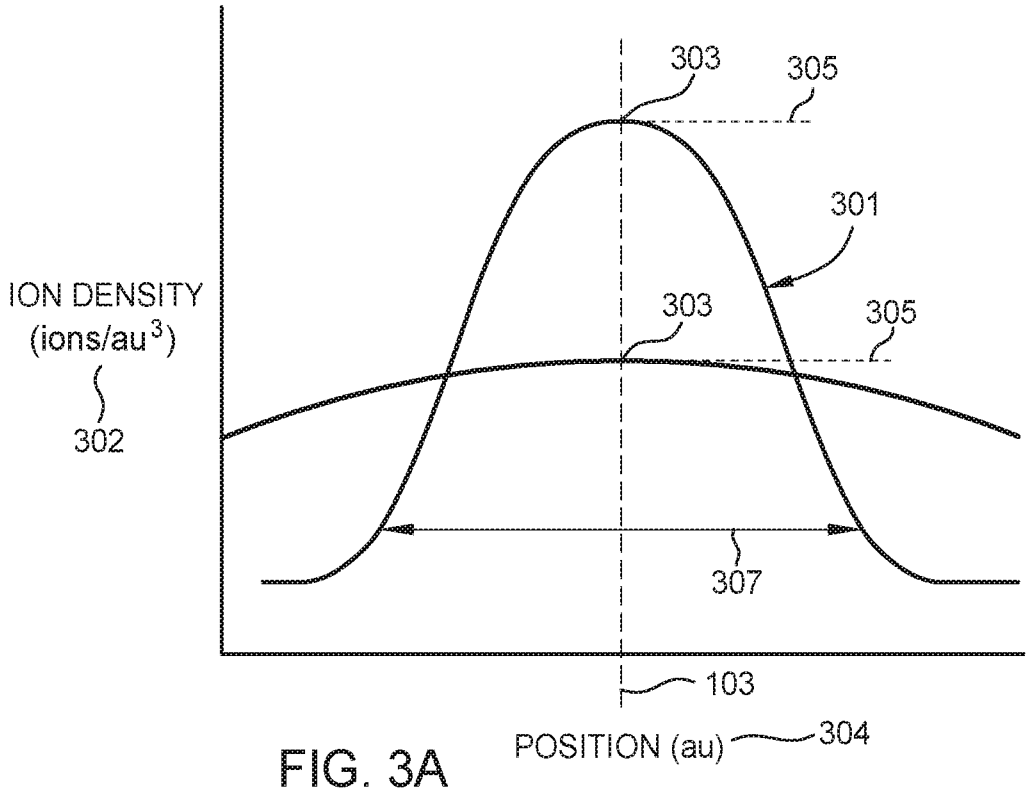
303
305
301
303
305
ION DENSITY
(ions/au3)
302
307
103
POSITION (au)
304

FIG. 3A

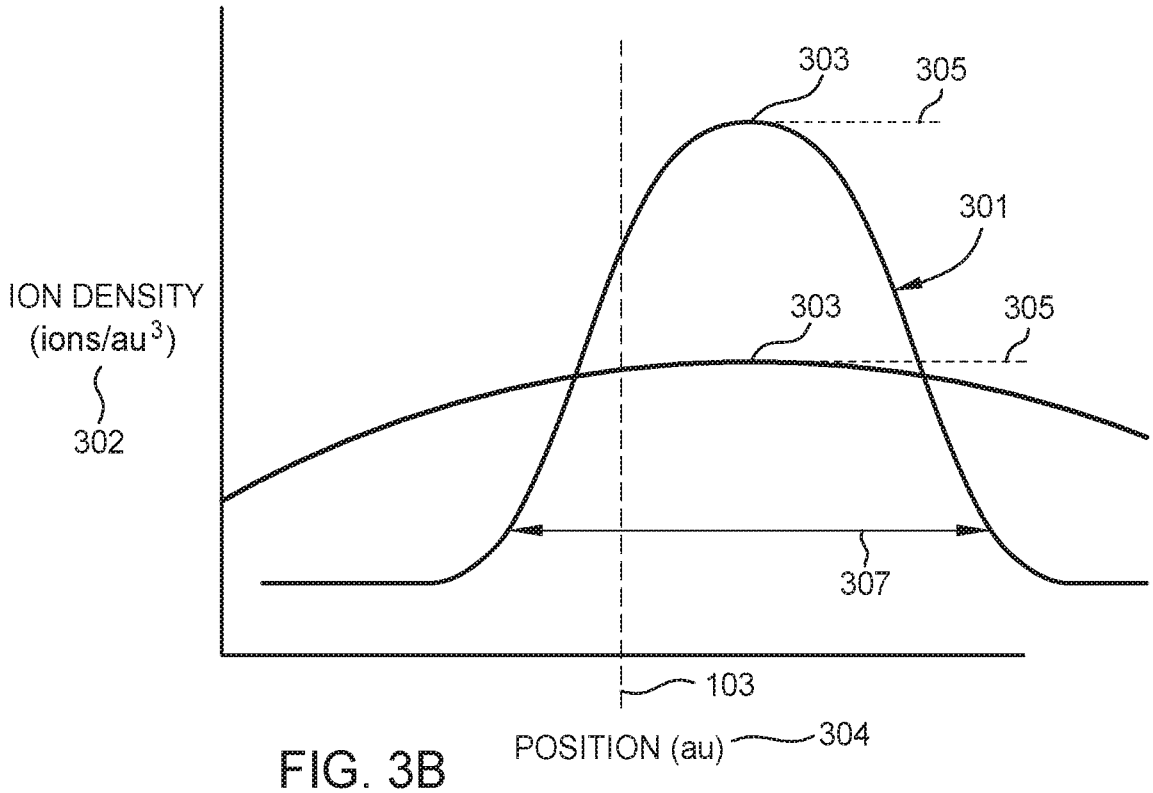
303
305
301
303
305
ION DENSITY
(ions/au3)
302
307
103
POSITION (au)
304

FIG. 3B